



## Si7403BDN vs. Si7403DN

**Description:** P-Channel, 20 V (D-S) MOSFET

**Package:** PowerPAK® 1212-8

**Pin Out:** Identical

**Part Number Replacements:**

Si7403BDN-T1-E3 Replaces Si7403DN-T1-E3

Si7403BDN-T1 Replaces Si7403DN-T1

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted					
Parameter	Symbol	Si7403BDN	Si7403DN	Unit	
Drain-Source Voltage	$V_{DS}$	- 20	- 20	V	
Gate-Source Voltage	$V_{GS}$	$\pm 8$	$\pm 8$		
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	$I_D$	- 5.1	- 4.5	A
	$T_A = 85\text{ }^\circ\text{C}$		- 4.1	- 3.2	
Pulsed Drain Current	$I_{DM}$	- 20	- 20		
Continuous Source Current (MOSFET Diode Conduction)	$I_S$	- 2.6	- 3.0		
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	$P_D$	3.1	3.5	
	$T_A = 85\text{ }^\circ\text{C}$		2	1.9	
Operating Junction and Storage Temperature Range	$T_j$ and $T_{stg}$	- 55 to 150	- 55 to 150	$^\circ\text{C}$	
Maximum Junction-to-Ambient	$R_{thJA}$	40	35	$^\circ\text{C/W}$	

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted									
Parameter	Symbol	Si7403BDN			Si7403DN			Unit	
		Min	Typ	Max	Min	Typ	Max		
<b>Static</b>									
Gate-Threshold Voltage	$V_{GS(th)}$	- 0.45		- 1.0	- 0.45		NS	V	
Gate-Body Leakage	$I_{GSS}$			$\pm 100$			$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$			- 1			- 1	$\mu\text{A}$	
On-State Drain Current	$V_{GS} = - 4.5\text{ V}$	$I_{D(on)}$	- 20		- 10			A	
	$V_{GS} = - 2.5\text{ V}$		NS		- 4				
Drain-Source On-Resistance	$V_{GS} = - 4.5\text{ V}$	$r_{DS(on)}$		0.059	0.074		0.078	0.100	$\Omega$
	$V_{GS} = - 2.5\text{ V}$			0.080	0.110		0.110	0.135	
Forward Transconductance	$g_{fs}$		10			8.8		S	
Diode Forward Voltage	$V_{SD}$		- 0.72	- 1.2		- 0.8	- 1.2	V	
<b>Dynamic</b>									
Total Gate Charge	$Q_g$		5.6	8.5		8.6	14	nC	
Gate-Source Charge	$Q_{gs}$		0.95			1.5			
Gate-Drain Charge	$Q_{gd}$		1.4			3.1			
Gate Resistance	$R_g$		10			NS		$\Omega$	
<b>Switching</b>									
Turn-On Time <sup>a</sup>	$t_{d(on)}$		5	10		27	50	ns	
	$t_r$		51	75		17	30		
Turn-Off Time <sup>a</sup>	$t_{d(off)}$		33	50		52	80		
	$t_f$		60	90		45	70		
Source-Drain Reverse Recovery Time	$t_{rr}$		20	40		50	80		

Notes:

a. Datasheet test conditions differ;  $R_L = 2.4\text{ }\Omega$ ,  $I_D = - 4.1\text{ A}$ ,  $R_g = 1\text{ }\Omega$  on the Si7403BDN and  $R_L = 10\text{ }\Omega$ ,  $I_D = - 1.6\text{ A}$ ,  $R_g = 6\text{ }\Omega$  on the Si7403DN.

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.